

	Type	Hits	Search Text	DBs	Time Stamp
13	BRS	81	((second! or another or addition\$ or third) near2 (anneal\$4 or heat\$4 or thermal\$4)) near8 ((ferroelectric or perovskite or PZT or (lead adj zirconium adj titanate)))	USPAT	2003/10/07 17:17
14	BRS	19732	third near2 (anneal\$4 or heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/22 16:07
15	BRS	19879	(RTA or RTP or (rapid adj thermal\$4 adj anneal\$4) or (rapid adj thermal\$4 adj process))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/22 16:07
16	BRS	3432	(second! or another or addition\$4) near2 (third near2 (anneal\$4 or heat\$4 or thermal\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/22 16:07

	Type	Hits	Search Text	DBs	Time Stamp
17	BRS	21	((RTA or RTP or (rapid adj thermal\$4 adj anneal\$4) or (rapid adj thermal\$4 adj process))) and ((second! or another or addition\$4) near2 (third near2 (anneal\$4 or heat\$4 or thermal\$4)))) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07
18	BRS	15574	(lead adj zirconium adj titanate) or PZT	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07
19	BRS	211185	(second! or another or addition\$ or third) near2 (anneal\$4 or heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07
20	BRS	62526	(ferroelectric or perovskite or PZT or (lead adj zirconium adj titanate))	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07

	Type	Hits	Search Text	DBs	Time Stamp
21	BRS	77	((RTA or RTP or (rapid adj thermal\$4 adj anneal\$4) or (rapid adj thermal\$4 adj process))) and ((second! or another or addition\$4) near2 (third near2 (anneal\$4 or heat\$4 or thermal\$4)))	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07
22	BRS	6	((((RTA or RTP or (rapid adj thermal\$4 adj anneal\$4) or (rapid adj thermal\$4 adj process))) and ((second! or another or addition\$4) near2 (third near2 (anneal\$4 or heat\$4 or thermal\$4)))) and capacitor) and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:12
23	BRS	3	(third near2 (anneal\$4 or heat\$4 or thermal\$4)) near8 ((lead adj zirconium adj titanate) or PZT)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07
24	BRS	17	(third near2 (anneal\$4 or heat\$4 or thermal\$4)) same ((lead adj zirconium adj titanate) or PZT)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	2004/12/22 16:07

	Type	Hits	Search Text	DBs	Time Stamp
25	BRS	83	((second! or another or addition\$ or third) near2 (anneal\$4 or heat\$4 or thermal\$4)) same ((lead adj zirconium adj titanate) or PZT)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 16:07
26	BRS	98	((second! or another or addition\$ or third) near2 (anneal\$4 or heat\$4 or thermal\$4)) near8 ((ferroelectric or perovskite or PZT or (lead adj zirconium adj titanate)))	USPAT	2004/12/22 16:07
27	BRS	80	S27 and ((@ad<"20001220") or (@rlad<"20001220"))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 16:19
28	IS&R	880	(438/239).CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 16:19

	Type	Hits	Search Text	DBs	Time Stamp
29	IS&R	1479	(438/3) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 16:20
30	IS&R	1193	(438/240) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 16:52
31	IS&R	107	(438/957) .CCLS.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 17:03

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	602030	capacitor	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
2	L2	16158	perovskite	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
3	L3	2264	second! adj anneal\$6	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
4	L4	121329	(top adj electrode) or (top adj plate) or (upper adj electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37

	L #	Hits	Search Text	DBs	Time Stamp
5	L6	485711 4	temperature or degree	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
6	L8	2589	first adj anneal\$6	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
7	L9	88	L7 and L8	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37
8	L5	104	L1 and L2 and L3 and L4	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37

	L #	Hits	Search Text	DBs	Time Stamp
9	L7	104	L5 and L6	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B	2004/12/22 15:37

US-PAT-NO: 6528863

DOCUMENT-IDENTIFIER: US 6528863 B1

TITLE: Perovskite-containing composite material,
method of manufacturing said material, electronic
component and module

----- KWIC -----

Application Filing Date - AD (1):
19950322

Brief Summary Text - BSTX (9):

With regard to this, a method of manufacturing a thin film from a ferroelectric perovskite material is described, for example, in U.S. Pat. No. 5,198,269, the contents of which are hereby incorporated by reference; said method comprising the following steps: a . providing a first substrate, b. selecting a first sol-gel-perovskite precursor material, the crystallization of this first sol-gel-perovskite precursor material to the perovskite phase being insensitive to the first substrate and, after the heat treatment, the material being isostructural relative to the second ferroelectric, perovskite thin-film material, c. depositing a first layer of the selected sol-gel-perovskite precursor material, d. subjecting said first layer to a thermal treatment to form a first ferroelectric, perovskite thin-film material, e. selecting a second sol-gel-perovskite precursor material, the crystallization of this second sol-gel-perovskite precursor material to the perovskite phase being sensitive to the substrate, f. depositing a second layer of the selected sol-gel-perovskite starting material, g. subjecting said second layer to a thermal treatment to form a second ferroelectric, perovskite thin-film material, the second layer of the second sol-gel-perovskite precursor

material,
after heat treatment, having better perovskite crystallinity when
deposited on
the first layer than if it would have been deposited directly on the
substrate
and heat treated.

US-PAT-NO: 6787412

DOCUMENT-IDENTIFIER: US 6787412 B2

TITLE: Dielectric element and method for fabricating
the same

----- KWIC -----

Detailed Description Text - DETX (122):

The series of steps from the application process to the second
heat
treatment were repeated four times, thereby forming a Bi-based
ferroelectric
thin film 8 having a thickness of 200 nm (FIG. 7).

Related Application Filing Date - RLFD (1):

20001113